Unit in mm

查询"2SA120300的pperTransistor Silicon PNP EPITAXIAL TYPE (PCT PROCESS)

2 S A 1 2 0 3

AUDIO FREQUENCY AMPLIFIER APPLICATIONS

- Suitable for Output Stage of 3 Watts Amplifier
- PC=1~2W (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SC2883

MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|-----------------------------|--------------------|---------|----------------------|
| Collector-Base Voltage | v_{CBO} | -30 | V |
| Collector-Emitter Voltage | v_{CEO} | -30 | V |
| Emitter-Base Voltage | v_{EBO} | -5 | V |
| Collector Current | $I_{\mathbf{C}}$ | -1.5 | Α |
| Base Current | $I_{\mathbf{B}}$ | -0.3 | Α |
| Collector Power Dissipation | PC | 500 | mW |
| Collector Power Dissipation | PC* | 1000 | mW |
| Junction Temperature | T_{j} | 150 | °C |
| Storage Temperature Range | $T_{ m stg}$ | -55~150 | $^{\circ}\mathrm{C}$ |

PC^{*} : Mounted on ceramic substrate (250mm²×0.8t)

4.6MAX. 1.7MAX. 0.4±0.05 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.6MAX. 0.4±0.05 0.4±0.05 0.4±0.05 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1

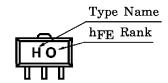
SC-62

2-5K1A

Weight: 0.05g Marking

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|---|------------------------|--|------|------|------|----------------|
| Collector Cut-off Current | I _{CBO} | $V_{CB} = -30V, I_{E} = 0$ | _ | _ | -0.1 | μ A |
| Emitter Cut-off Current | I_{EBO} | $V_{EB} = -5V, I_{C} = 0$ | _ | _ | -0.1 | μ A |
| Collector-Emitter Breakdown Voltage | V (BR) CEO | $I_{\rm C} = -10 {\rm mA}, \ I_{\rm B} = 0$ | -30 | _ | _ | v |
| Emitter-Base Breakdown Voltage | V (BR) EBO | $I_{E} = -1 \text{mA}, I_{C} = 0$ | -5 | _ | _ | V |
| DC Current Gain | h _{FE} (Note) | $V_{CE} = -2V, I_{C} = -500 \text{mA}$ | 100 | _ | 320 | |
| Collector-Emitter Saturation Voltage | V _{CE (sat)} | $I_C = -1.5A, I_B = -0.03A$ | _ | _ | -2.0 | V |
| Base-Emitter Voltage | $V_{ m BE}$ | $V_{CE} = -2V, I_{C} = -500 \text{mA}$ | _ | _ | -1.0 | V |
| Transition Frequency | $\mathbf{f_T}$ | $V_{CE} = -2V, I_{C} = -500 \text{mA}$ | _ | 120 | _ | MHz |
| Collector Output Capacitance | $\mathrm{C_{ob}}$ | $V_{CB} = -10V, I_E = 0, f = 1MHz$ | _ | _ | 50 | рF |

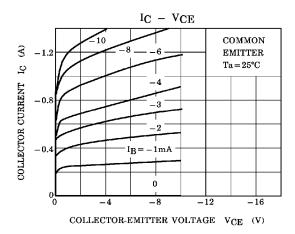
Note: hFE Classification O: 100~200, Y: 160~320

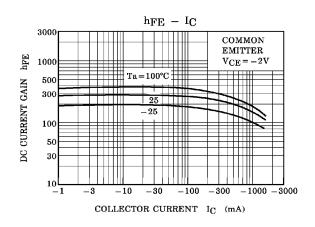
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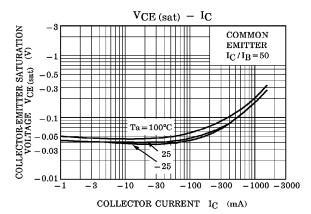
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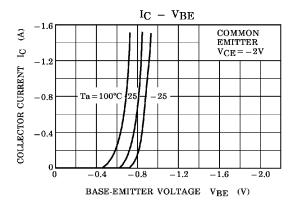
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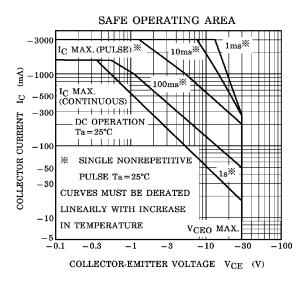
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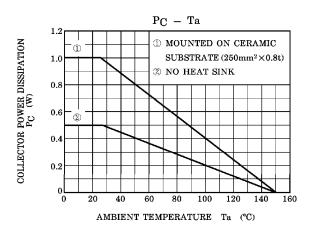












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